



### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-30V	$42m\Omega @ V_{GS} = -10V$	-5.1A
-307	65mΩ @ V <sub>GS</sub> = -4.5V	-4.0A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

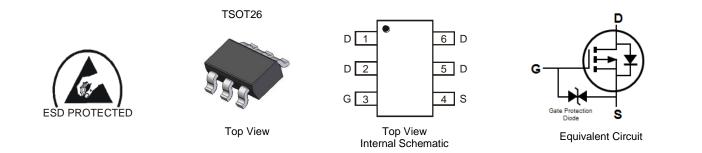
#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.015 grams (Approximate)



#### Ordering Information (Note 4)

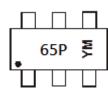
Part Number	Case	Packaging
DMP3065LVT-7	TSOT26	3,000/Tape & Reel
DMP3065LVT-13	TSOT26	10,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### Marking Information



65P = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2011		2012	2013		2014	2015		2016	2017		2018
Code	Y		Z	А		В	С		D	E		F
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### Maximum Ratings P-Channel (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-5.1 -4.2	A
Continuous Drain Current (Note 5) $V_{GS}$ = -4.5V	ID	-4.0 -3.2	А		
Maximum Body Diode Continuous Current		I <sub>S</sub>	-2.0	А	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	102	°C/W
Total Power Dissipation (Note 5)		PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	78	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

#### Electrical Characteristics P-Channel (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			•	•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	—	V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current $@T_J = +25^{\circ}C$	IDSS		_	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	-1.7	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Statia Duria Course On Desistance	5		34	42		V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.9A	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	52	65	mΩ	$V_{GS} = -4.5V, I_D = -3.7A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	8.5	_	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4.9A	
Diode Forward Voltage		_	-0.75	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	587	880			
Output Capacitance		_	160	240	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	84	130			
Total Gate Charge (V <sub>GS</sub> = -4.5V)		_	6.3	10			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	12.3	20	nC	$V_{DS} = -15V, I_D = -4.9A$	
Gate-Source Charge	Q <sub>gs</sub>	_	1.9	4			
Gate-Drain Charge	Q <sub>gd</sub>	_	2.5	5	1		
Turn-On Delay Time		_	5.7	10			
Turn-On Rise Time			11.8	22	ns	$V_{DD}$ = -15V, $V_{GS}$ = -10V, $I_D$ = -4.9A, $R_G$ = 6 $\Omega$	
Turn-Off Delay Time		_	21.8	35			
Turn-Off Fall Time	t <sub>f</sub>	_	23.9	40			

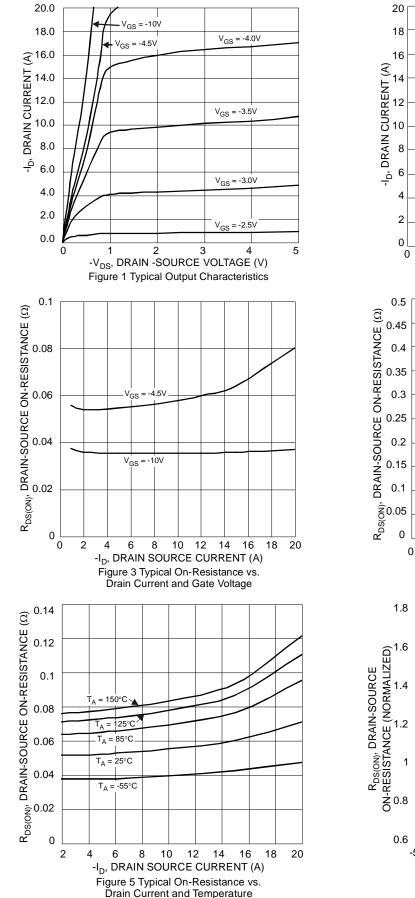
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

### DMP3065LVT





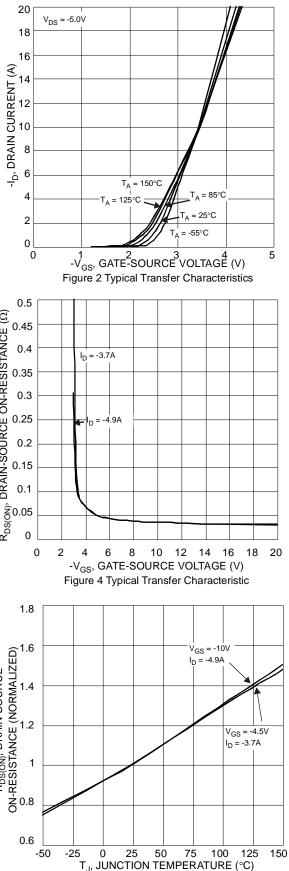
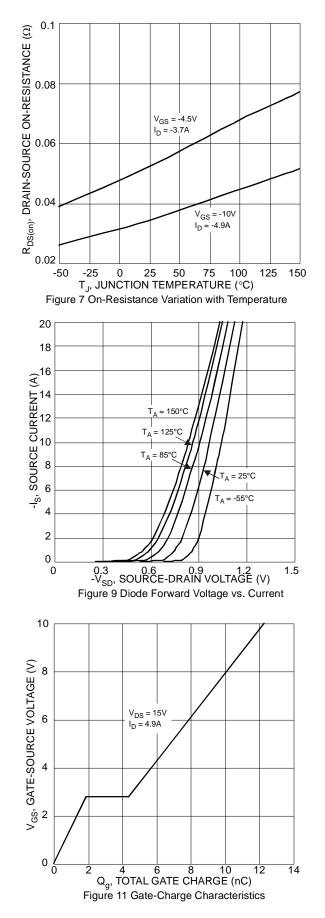
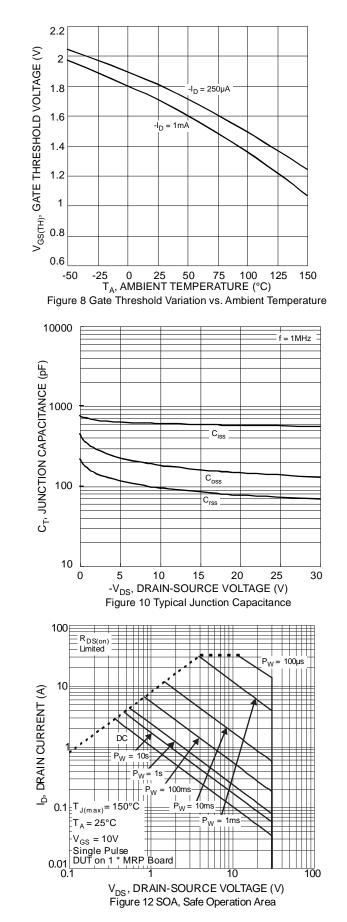


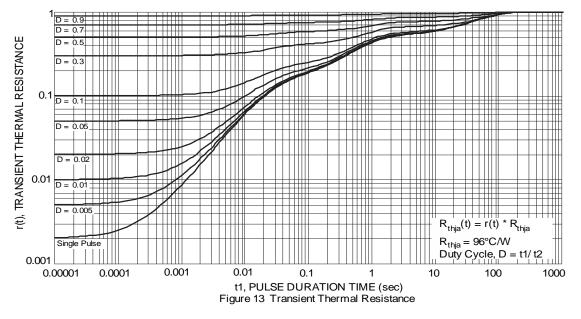
Figure 6 On-Resistance Variation with Temperature





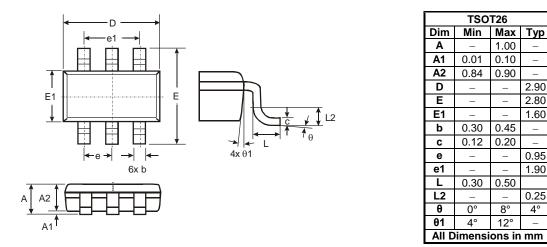






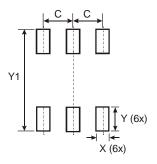
## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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# Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

- > Sales :
  - Direct +86 (21) 6401-6692
  - Email amall@ameya360.com
  - QQ 800077892
  - Skype ameyasales1 ameyasales2

# > Customer Service :

Email service@ameya360.com

# > Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com